12/1/2000



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U.S. DEPARTMENT OF COMMERCE 1-31-92 S ONL®Y 101536243 Tab settings ⇔ ⇔ ⇔ B10-25562US▼ To the Honorable Commissioner of Patents and Trademarks: Please record the attached of analytic cuments or copy thereof. Name of conveying party(ies): Name and address of receiving party(ies): Shaoping Li, Theodore Zhu, Anthony S. Arrott, Name: Honeywell Inc. Harry Liu, William L. Larson, Yong Lu Internal Address: Honeywell International Inc. 8 Additional name(s) of conveying party(ies) attached? ☐ Yes ☒ No Street Address: 101 Columbia Road 3. Nature of conveyance: P.O. Box 2245 Merger Security Agreement Change of Name Other City: Morristown State: NJ ZIP: 07962-2245 **Execution Date:** 11/14/00, 10/13/00, 10/23/00, 10/16/00 Additional name(s) & address(es) attached? ☐ Yes X No Application number(s) or patent number(s): 09/618,504 If this document is being filed together with a new application, the execution date of the application is: A. Patent Application No.(s) 09/618,504 B. Patent No. (s) Additional numbers attached? ☐ Yes X No Name and address of party to whom correspondence 6. Total number of applications and patents involved: concerning document should be mailed: Name: Kris T. Fredrick Internal Address: Honeywell International Inc. 7. Total fee (37 CFR 3.41) \$40.00 Street Address: 101 Columbia Road. **Enclosed** P.O. Box 2245 Authorized to be charged to deposit account Deposit account number: 01-1125 City: Morristown State: NJ ZIP: 07962-2245 DO NOT USE THIS SPACE /01/2000 MTHAI1 00000314 011125 09618504 FC:581 40.00 CH 9. Statement and signature. To the best of my knowledge and belief, the foregoing information is true and correct and any attached copy is a true copy of the original document. Kris T. Fredrick Name of Person Signing Signature

Total number of pages of attached conveyance document (including attachments):



JOINT PATENT

FILE NO. B10-25562US

### **ASSIGNMENT**

WHEREAS, SHAOPING LI of NAPERVILLE, County of WILL, and State of ILLINOIS, THEODORE ZHU of MAPLE GROVE, County of HENNEPIN, and State of MINNESOTA, ANTHONY S. ARROTT of WASHINGTON, D.C. DISTRICT OF COLUMBIA, HARRY LIU of PLYMOUTH, County of HENNEPIN, and State of MINNESOTA, WILLIAM L. LARSON of EDEN PRAIRIE, County of HENNEPIN, and State of MINNESOTA have invented certain new and useful improvements in MRAM ARCHITECTURES FOR INCREASED WRITE SELECTIVITY for which an application is about to be made for Letters Patent of the United States, said application having been executed on the 14th day of Nov. 2000, the 13th day of Och 2000 the 33rd day of Och 2000 13th day of Och 2000 13th day of Och 2000, 13th

Whereas, Honeywell International Inc., a corporation organized and existing under the laws of the State of Delaware, and having its principal offices at 101 Columbia Road, P.O. Box 2245, Morristown, NJ 07962-2245 U.S.A. is desirous of acquiring the entire right, title and interest in and to said invention, said application and in, to and under any and all Letters Patent to be obtained therefor;

Now, therefore, for good and valuable consideration to us paid by the said Honeywell International Inc., the receipt of which is hereby acknowledged, we have sold, assigned and transferred, and by these presents do hereby sell, assign and transfer unto the said Honeywell International Inc., its successors and assigns, our entire right, title and interest in and to said invention, said application and the Letters Patent, both foreign and domestic, that may or shall issue, including all of our rights under any and all international conventions, treaties and/or agreements concerning patents to which the United States is a party, and we do hereby authorize and request the Commissioner of Patents to issue said Letters Patent to the above mentioned assignee in accordance herewith.

We further authorize said assignee, its successors and assigns, or anyone it may properly designate, to apply for Letters Patent, in its own name if desired, in any and all foreign countries, and additionally to claim the filing date of said United States application and/or otherwise take advantage of the provisions of any international convention, treaty and/or agreement.

We do hereby covenant and agree with the said assignee, its successors and assigns, that we will not execute any writing or do any act whatsoever conflicting with these presents, and that we or our executors or administrators will at any time upon request, without further or additional consideration, but at the expense of the said assignee, its successors and assigns, execute such additional writings and do such additional acts as said assignee, its successors and assigns, may deem necessary or desirable to perfect the assignee's enjoyment of this grant, and render all necessary assistance in making application for and obtaining original, divisional, reissued or extended Letters Patent of the United States, or any of and all foreign countries on said invention, and in enforcing any rights, occurring as a result of such applications or patents, by giving testimony in any proceedings or transactions involving such applications or patents.

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	PYCO
- Moura Arro III	Shaso Coli
Date NOVEMBER 14, 2000	SHAOPING LI
State of MINDESOTA	
\on	•
County of DAKOTA )ss.	
On this 14 day of NOVEMBER, 2000, be to be the person described in and who executed the foregoing in free act and deed.	ofore me personally appeared SHAOPING LI, to me known astrument and acknowledged that he executed the same as his
	Prairie a. Ram theen
MARCIA A. FIAMTHUN NOTARY PUBLIC-MINNESOTA MY COMMISSION EXPIRES 1-31-2005	Notary Public, County DAKOTA State of M NNESOTA My Commission Expires 1-362005
	4 04
Date October 13, 2000	THEODORE ZHU
State of Messenta	
County of Herry )ss.	•
On this Latte day of October 2000 be	fore me personally appeared THEODORE ZHU, to me known
to be the person described in and who executed the foregoing in	strument and acknowledged that he executed the same as his free
act and deed.	0-104
	Notary Public, County Henry
JANET R. GORMAN NOTARY PUBLIC - MINNESOTA My Commission Expires Jan. 31, 2005	State of The My Commission Expires 1-31-2005
***************************************	
Date 10/23 ,2000	ANTHONY S. ARROTT
State of Deresta	
County of	
On this 23 rd day of October, 2000, b	efore me personally appeared ANTHONY S. ARROTT, to me
known to be the person described in and who executed the fore	going instrument and acknowledged that he executed the same as

Notary Public, County Heaven State of Messes Jan. 31, 2005

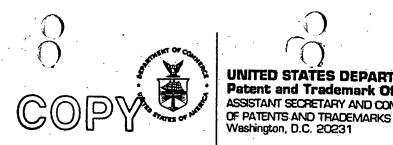


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Date October 13 , 2000	I fully
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State of Herresota )	
County of Henreper	·
and the fitting	
the person described in and who executed the foregoing instrument	e me personally appeared HARRY LIU, to me known to be
and deed.	t and acknowledged that he executed the same as his free act
	( ) - P /S
JANET R. GORMAN	Notary Public County Herris
NOTARY PUBLIC - MINNESOTA	State of Mennit
My Commission Emires, Jan. 21, 2005	My Commission Expires /-3/-2005
···· ···· ····························	2 /
Date Oct. 16 .2000	Willan Fran
(100	WILLIAM L. LARSON
State of Minisotic )	
County of Hampen )ss.	
the state of	
On this 16 4 day of October, 2000, befor	e me personally appeared WILLIAM L. LARSON, to me
known to be the person described in and who executed the foregoing his free act and deed.	ng instrument and acknowledged that he executed the same as
\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	Caller Sue Dufort
COLLEEN SUE DUPONT	
MINNESOTA	State of
My Commission Expires Jan. 31, 2005	My Commission Expires Qun. 31, 20 of
	·
Date 10 / 13 , 2000	
2000	YONG LU
State of Minnesota	
County of Hennepin )ss.	
· <del>-</del>	e me personally appeared YONG LU, to me known to be the
person described in and who executed the foregoing instrument an deed.	d acknowledged that he executed the same as his free act and



Notary Public, County
State of Manual My Commission Expires /-

Doc:Assign-J



FEBRUARY 02, 2001

HONEYWELL INTERNATIONAL INC. KRIS T. FREDRICK 101 COLUMBIA ROAD P.O. BOX 2245 MORRISTOWN, NJ 07962-2245

Patent and Trademark Office ASSISTANT SECRETARY AND COMMISSIONER

Washington, D.C. 20231

UNITED STATES PATENT AND TRADEMARK OFFICE NOTICE OF RECORDATION OF ASSIGNMENT DOCUMENT

THE ENCLOSED DOCUMENT HAS BEEN RECORDED BY THE ASSIGNMENT DIVISION OF THE U.S. PATENT AND TRADEMARK OFFICE. A COMPLETE MICROFILM COPY IS AVAILABLE AT THE ASSIGNMENT SEARCH ROOM ON THE REEL AND FRAME NUMBER REFERENCED BELOW.

PLEASE REVIEW ALL INFORMATION CONTAINED ON THIS NOTICE. THE INFORMATION CONTAINED ON THIS RECORDATION NOTICE REFLECTS THE DATA PRESENT IN THE PATENT AND TRADEMARK ASSIGNMENT SYSTEM. FIND ANY ERRORS OR HAVE QUESTIONS CONCERNING THIS NOTICE, YOU MAY CONTACT THE EMPLOYEE WHOSE NAME APPEARS ON THIS NOTICE AT 703-308-9723. PLEASE SEND REQUEST FOR CORRECTION TO: U.S. PATENT AND TRADEMARK OFFICE, ASSIGNMENT DIVISION, BOX ASSIGNMENTS, CG-4, 1213 JEFFERSON DAVIS HWY. SUITE 320, WASHINGTON, D.C. 20231.

RECORDATION DATE: 11/20/2000

REEL/FRAME: 011283/0195

NUMBER OF PAGES: 4

BRIEF: ASSIGNMENT OF ASSIGNOR''S INTEREST (SEE DOCUMENT FOR DETAILS).

ASSIGNOR:

LI, SHAOPING

DOC DATE: 11/14/2000

ASSIGNOR:

ZHU, THEODORE

DOC DATE: 10/13/2000

ASSIGNOR:

ARROTT, ANTHONY S.

DOC DATE: 10/23/2000

ASSIGNOR:

LIU, HARRY

DOC DATE: 10/13/2000

ASSIGNOR:

LARSON, WILLIAM L.

DOC DATE: 10/16/2000

ASSIGNOR:

LU, YONG

DOC DATE: 10/13/2000

RECEIVED

FEB 1 3 2001

HONEYWELL LEGAL

# 011283/0195 PAGE 2



# ASSIGNEE:

HONEYWELL INC. HONEYWELL INTERNATIONAL INC. 101 COLUMBIA ROAD - P.O. BOX 2245 MORRISTOWN, NEW JERSEY 07962-2245

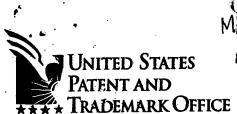
SERIAL NUMBER: 09618504

PATENT NUMBER:

FILING DATE: 07/18/2000

ISSUE DATE:

SHAREILL COLES, EXAMINER ASSIGNMENT DIVISION OFFICE OF PUBLIC RECORDS



MORON, 198A R.S. ASA · MSO



MAY 29, 2002

PTAS

KNOBBE, MARTENS, OLSON & BEAR, LLP ADEEL S. AKHTAR 620 NEWPORT CENTER DRIVE SIXTEENTH FLOOR NEWPORT BEACH, CA 92660 Chief Information Officer Washington, DC 20231 www.uspto.gov



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RECORDATION DATE: 09/28/2001

REEL/FRAME: 012735/0417

NUMBER OF PAGES: 8

BRIEF: ASSIGNMENT OF ASSIGNOR'S INTEREST (SEE DOCUMENT FOR DETAILS).

ASSIGNOR:

HONEYWELL INTERNATIONAL, INC.

DOC DATE: 12/18/2000

ASSIGNEE:

MICRON TECHNOLOGY, INC. 8000 SOUTH FEDERAL WAY P.O. BOX 6 BOISE, IDAHO 83707-0006

SERIAL NUMBER: 09318073

FILING DATE: 05/25/1999

ISSUE DATE:

SERTAL NUMBER: 09618237

FILING DATE: 07/18/2000

ISSUE DATE:

SERIAL NUMBER: 09618256 PATENT NUMBER: 6396733 FILING DATE: 07/17/2000 ISSUE DATE: 05/28/2002

SERIAL NUMBER: 09618492

FILING DATE: 07/18/2000

PATENT NUMBER:

PATENT NUMBER:

PATENT NUMBER:

ISSUE DATE:



#### 012735 0417 PAGE 2

SERIAL NUMBER: 09618504 / FILING DATE: 07/18/2000 /

PATENT NUMBER: ISSUE DATE:

SERIAL NUMBER: 09638415 FILING DATE: 08/14/2000 PATENT NUMBER: 6363007 ISSUE DATE: 03/26/2002

SERIAL NUMBER: 09638419 FILING DATE: 08/14/2000 PATENT NUMBER: 6392922 ISSUE DATE: 05/21/2002

SERIAL NUMBER: 09638637 FILING DATE: 08/14/2000

PATENT NUMBER: ISSUE DATE:

SERIAL NUMBER: 09668922 FILING DATE: 09/25/2000

PATENT NUMBER: ISSUE DATE:

SERIAL NUMBER: 08962512 FILING DATE: 10/31/1997 PATENT NUMBER: 5939772 ISSUE DATE: 08/17/1999

SERIAL NUMBER: 08993009 FILING DATE: 12/18/1997
PATENT NUMBER: 5956267 ISSUE DATE: 09/21/1999

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PATENT NUMBER: 5982658 FILING DATE: 11/09/1999

SERIAL NUMBER: 08940587 FILING DATE: 09/30/1997
PATENT NUMBER: 6027948 FILING DATE: 02/22/2000

SERIAL NUMBER: 08993005 FILING DATE: 12/18/1997
PATENT NUMBER: 6048739 ISSUE DATE: 04/11/2000

SERIAL NUMBER: 09365308 FILING DATE: 07/30/1999
PATENT NUMBER: 6134138 FILING DATE: 10/17/2000

SERIAL NUMBER: 09396189 FILING DATE: 09/14/1999
PATENT NUMBER: 6147922 ISSUE DATE: 11/14/2000

 SERIAL NUMBER: 09429664
 FILING DATE: 10/28/1999

 PATENT NUMBER: 6175525
 ISSUE DATE: 01/16/2001

 SERIAL NUMBER: 09455850
 FILING DATE: 12/07/1999

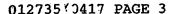
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 ISSUE DATE: 01/23/2001

SERIAL NUMBER: 09059871 FILING DATE: 04/14/1998 PATENT NUMBER: 6269027 ISSUE DATE: 07/31/2001

SERIAL NUMBER: 06879679 FILING DATE: 06/27/1986
PATENT NUMBER: 4731757 ISSUE DATE: 03/15/1988

SERIAL NUMBER: 06908075 FILING DATE: 09/16/1986 PATENT NUMBER: 4751677 ISSUE DATE: 06/14/1988

SERIAL NUMBER: 07008211 FILING DATE: 01/28/1987
PATENT NUMBER: 4754431 ISSUE DATE: 06/28/1988



SERIAL NUMBER: 06870068 FILING DATE: 06/03/1986
PATENT NUMBER: 4780848 FILING DATE: 10/25/1988

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SERIAL NUMBER: 07078612 FILING DATE: 07/28/1987
PATENT NUMBER: 4829476 ISSUE DATE: 05/09/1989

SERIAL NUMBER: 07168293 FILING DATE: 03/15/1988
PATENT NUMBER: 4897288 ISSUE DATE: 01/30/1990

SERIAL NUMBER: 07161534 FILING DATE: 02/29/1988 PATENT NUMBER: 4918655 FILING DATE: 04/17/1990

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PATENT NUMBER: 4953002 ISSUE DATE: 08/28/1990

SERIAL NUMBER: 07504777 FILING DATE: 04/04/1990 PATENT NUMBER: 5012444 FILING DATE: 04/30/1991

 SERIAL NUMBER:
 07505090
 FILING DATE:
 04/04/1990

 PATENT NUMBER:
 5060193
 ISSUE DATE:
 10/22/1991

SERIAL NUMBER: 07507682 FILING DATE: 04/09/1990 PATENT NUMBER: 5064499 ISSUE DATE: 11/12/1991

SERIAL NUMBER: 08061603 FILING DATE: 05/13/1993
PATENT NUMBER: 5349302 FILING DATE: 09/20/1994

SERIAL NUMBER: 08365852 FILING DATE: 12/29/1994
PATENT NUMBER: 5496759 ISSUE DATE: 03/05/1996

SERIAL NUMBER: 08576279 FILING DATE: 12/21/1995
PATENT NUMBER: 5569617 FILING DATE: 10/29/1996

 SERIAL NUMBER: 08576732
 FILING DATE: 12/21/1995

 PATENT NUMBER: 5756366
 ISSUE DATE: 05/26/1998

SHARON BROOKS, EXAMINER ASSIGNMENT DIVISION OFFICE OF PUBLIC RECORDS

Client Code: MICRON.173GEN 102101707 E ASSISTANT COMMISSIONER FOR L. uments or copy thereof 2. Name and address of receiving party(ies): 1. Name of conveying party(ies): (If multiple assignors, list numerically) Name: Micron Technology, Inc. Internal Address: P.O. Box 6 H neywell International, Inc. Street Address: 8000 South Federal Way City: Boise State: Idaho ZIP: 83707-0006 Additional name(s) of conveying party(ies) attached? No Yes (X) Additional name(s) of receiving party(ies) attached? No (X) () Application number(s) or Patent number(s): Nature of conveyance: () Application(s) filed herewith Execution Date(s): (x) Assignment - Nunc Pro Tunc Merger Patent Application No.: See ATTACHMENT A 19348 673 (x) Security Agreement Filing Date: See ATTACHMENT A Change of Name Other: Patent No.: See ATTACHMENT B Issue Date: See ATTACHMENT B Execution Date: (If multiple assignors, list execution dates in numerical order corresponding to numbers indicated in (X) No Additional numbers attached? () 1 above) December 18, 2000 Total fee (37 CFR 1.21(h)): \$1,360 Name and address of party to whom correspondence concerning document should be mailed: (X) Enclosed Authorized to be charged to deposit account 0 Adeel S. Akhtar KNOBBE, MARTENS, OLSON & BEAR, LLP Customer No. 20,995 Internal Address: Sixteenth Floor Deposit account number: 11-1410 Street Address: 620 Newport Center Drive Please charge this account for any additional fees which City: Newport Beach State: CA ZIP: 92660 Attorney's Docket No.: MICRON.173GEN be required, or credit any overpayment to this accounts  $\nabla$ Total number of applications and patents involved: 34 Statement and signature. To the best of my knowledge and belief, the foregoing information is true and correct, and any attached copy is a true copy of the original document. Adeel S. Akhtar Name of Person Signing Registration No.41,394 Total number of pages including cover sheet, attachments and document: 8 Mail documents to be recorded with required cover sheet information t:

> U.S. Patent and Trademark Office Attn: Assignment Division

> > Crystal Gateway-4

1213 Jefferson Davis Highway, Suit 320 Arlington, VA 22202

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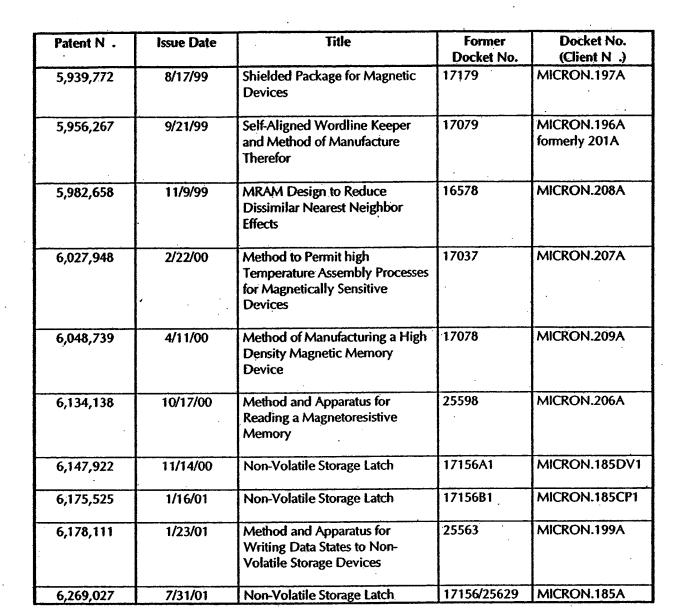
FC:581



# ATTACHMENT A PENDING PATENTS

Serial No.	Filing Date	Title	Former Docket No.	Docket No. (Client No.)
09/318,073	5/25/99	Local Shielding for Memory Cells	25561	MICRON.196CP1
09/618,237	7/18/00	Magneto-Resistive Memory Array	26090	MICRON.211A
09/618,256	7/17/00	Magneto-Resistive Memory Having Sense Amplifier with Offset Control	26310	MICRON.210A
09/618,492	7/18/00	Memory Redundancy with programmable Non-Volatile Control	26083	MICRON.212A
09/618,504	7/18/00	MRAM Architectures for Increased Write Selectivity	25562	MICRON.198A
09/638,415	8/14/00	Magneto-Resistive Memory with Shared Wordline and Sense Line	26091	MICRON.213A
09/638,419	8/14/00	Passivated Magneto-Resistive Bit Structure and Passivation Method Therefor	25637	MICRON.214A
09/638,637	8/14/00	Pulsed Write Techniques for Magneto-Resistive Memories	26025	MICRON.215A
. 09/668,922	9/25/00	Shielding Arrangement to Protect A Circuit From Stray Magnetic Fields	26347	MICRON.216A

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# ATTACHMENT B ISSUED PATENTS



Patent No.	Issue Date	Title	Former Docket No.	Docket No. (Client No.)
4,731,757	3/15/88	Magnetoresistive Memory Including Thin Film Storage Cells Having Tapered Ends	10790	MICRON.189A
4,751,677	6/14/88	Differential Arrangement Magnetic Memory Cell	11874	MICRON.187A
4,754,431	6/28/88	Vialess Shorting Bars for Magnetoresistive Devices	12062	MICRON.195A
4,780,848	10/25/88	Magnetoresistive Memory with Multi-Layer Storage Cells Having layers of Limited Thickness	10789	MICRON.188A
4,829,476	5/9/89	Differential Magnetoresistive Memory Sensing	12056	MICRON.186A
4,897,288	1/30/90	Vialess Shorting Bars for Magnetoresistive Devices	12724	MICRON.192DV1
4,918,655	4/17/90	Magnetic Device Integrated Circuit Interconnection System	12092	MICRON.194A
4,953,002 .	8/28/90	Semiconductor Device Housing with Magnetic Field Protection	12035	MICRON:203FW1
5,012,444	4/30/91	Opposed Field Magnetoresistive Memory Sensing	13117	MICRON.191A
5,060,193	10/22/91	Magnetic State Entry Assurance	13268	MICRON.190A
5,064,499	11/12/91	Inductively Sensed Magnetic Memory	12173	MICRON.193A
5,349,302	9/20/94	Sense Amplifier Input Stage for Single Array Memory	13490	MICRON.202A
5,496,759	3/5/96	Highly Producivle Magnetoresistive RAM Process	15742	MICRON.204A
5,569,617	10/29/96	Integrated Spacer for Magnetoresistive RAM	16139	MICRON.205A
5,756,366	5/26/98	Magnetic hardening of Bit Edges of Magnetoresistive RAM	16251	MICRON.200A



#### NUNC PRO TUNC ASSIGNMENT

Effective as of December 18, 2000, Honeywell International Inc., a Delaware corporation, acting through its Solid State Electronics Center having a principal place of business at 12001 State Hwy 55, Plymouth, Minnesota, and Honeywell Intellectual Properties Inc., an Arizona corporation having a principal place of business at 8440 South Hardy Dr., Tempe, Arizona (collectively referred to as "Honeywell") hereby make the following assignments for good and valuable consideration to Micron Technology Inc., a Delaware corporation having a principal place of business at 8000 S. Federal Way, Boise, Idaho: all right, title, and interest in the patents and patent applications listed in Appendix A and any of their related continuation, continuation-in-part, divisional or reissue applications or patents and any foreign counterpart applications or patents which now exist or which may later exist.

MICRON TECHNOLOGY, INC.

Signature: 12

Printed Name: M: WL, Cyml.

Title: Ching Pott Council

HONEYWELL INTERNATIONAL, INC.

Signature:

Printed Name: DAVID S. Howker

Title: Cheft Partor Cosaule

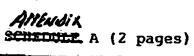
HONEYWELL INTELLECTUAL

PROPERTIES, INC

Signature: Jent Alons

Printed Name: Kent Aosms

Title: DIRECTOR - LICENSING





Patent Number  SUGI Patents  A781/877 MAGNETIC MEMORY CONFIGURATION HAVAIT, 31/898 Japantu  A781/877 HIGH SPEED MIR MEMORY  MAGNETIC RESISTIVE MEMORY  MAGNETIC RESISTIVE MEMORY  MAGNETIC RESISTIVE MEMORY  MAGNETIC RESISTIVE MEMORY  A29,876 ADTERPRINTAL CREAT ACCRETICATION OF AMOUNT OF		SSEC MRAMIN	itellectual Property			
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Pending Patent	Applications :		 with a contract of the	
Docket Number	file a sale of	First Inventor	Filing Date	Countries Filed 1
25561	LOCAL SHIELDING FOR MEMORY CELLS	SATHER, Jeffrey Scott	 5/25/99	US/PCT/Taiw
25562	MANAM ARCHIECTURES FOR INCREASED	AAROTT, Anthony S.	7/18/00	us
25563	METHOD AND APPARATUS FOR WRITING DATA STATES TO NON-VOLATILE STORAGE DEVICES	LU, Yang	12/7/99	US



25598	METHOD AND APPARATUS FOR READING A MAGNETORESISTIVE MEMORY	LU, Yong	7/30/99	us
26025	MAGNETO-RESISTIVE MEMORY WITH SHARE WORDLINE AND SENSE LINE	JOHNSON, William J.	9/14/00	us
26083	MEMORY REDUNDANCY WITH PROGRAMMABLE NON-VOLATILE CONTROL	KIRCHNER, Gary D.	7/18/00	us
26090	MAGNETOC-RESISTIVE MEMORY ARRAY	KATTI, Romney R.	7/18/00	us
26091		KATTI, Romney R.	8/14/00	us
26310	MAGNETO-RESISTIVE MEMORY HAVING SENSE AMPLIFIER WITH OFFSET CONTROL	ORIES, Michael Frederick	7/18/00	us
1715G/25629	NON-VOLATILE STORAGE ELEMENT	GADBOIS, Jason B.	4/14/98	us
17156A1	NON-VOCATILE STORAGE ELEMENT	GADBOIS, Jason B.	9/14/99	us
1715681	NON-VOLATILE STORAGE ELEMENT	GADBOIS, Jason B.	10/28/99	us
17156US	NON-VOLATILE STORAGE ELEMENT	GADBOIS, Jason B.	4/14/98	US/PCT
	PASSIVATED MAGNETO-RESTRICTIVE BIT STRUCTURE AND PASSIVATION METHOD		25470	us
25637/26028	THEREFOR	BERG, Lonny L.	8/14/00	105